

Description

The PMV40UN2R uses advanced trench technology

to provide excellent $R_{\text{DS}(\text{ON})}$, low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



PIN2 D

General Features

 $V_{DS} = 30V I_{D} = 5A$

$R_{DS(ON)}$ < 42m Ω @ V_{GS} =10V**Application**

Battery protection

Load switch

Uninterruptible power supply

N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
PMV40UN2R	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	30	V
V _G s	Gate-Source Voltage	±12	V
I _D	Drain Current-Continuous	5	Α
Ідм	Drain Current-Pulsed (Note 1)	14.4	А
P _D	Maximum Power Dissipation	1	W
Тл,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	125	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V	
Danier	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =3A		33	42	mΩ	
R _{DS(ON)}		V _{GS} =4.5V , I _D =2A		38	48		
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.4		1.2	V	
Ipss	Drain-Source Leakage Current	V _{DS} =16V , V _{GS} =0V , T _J =25°C			1	- uA	
IDSS		V _{DS} =16V , V _{GS} =0V , T _J =55°C			5		
Igss	Gate-Source Leakage Current	$V_{GS}=\pm 12V$, $V_{DS}=0V$			±100	nA	
gfs	Forward Transconductance	V _{DS} =5V , I _D =3A		10.5		S	
Qg	Total Gate Charge (4.5V)			4.6			
Qgs	Gate-Source Charge	V _{DS} =15V , V _{GS} =4.5V , I _D =3A		0.7		nC	
Q_{gd}	Gate-Drain Charge			1.5			
T _{d(on)}	Turn-On Delay Time			1.6			
Tr	Rise Time	V_{DD} =10V , V_{GS} =4.5V , R_{G} =3.3 Ω		42			
T _{d(off)}	Turn-Off Delay Time	I _D =3A		14		ns	
Tf	Fall Time			7			
C _{iss}	Input Capacitance			310			
Coss	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		49		pF	
Crss	Reverse Transfer Capacitance			35			

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,4}	V _G =V _D =0V , Force Current	-		3.6	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C			1.2	V

Note:

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\,\leq\,300\text{us}$, duty cycle $\,\leq\,2\%$
- 3.The power dissipation is limited by 150°C junction temperature
- 4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

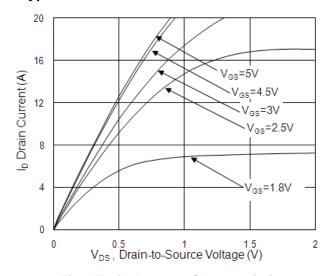


Fig.1 Typical Output Characteristics

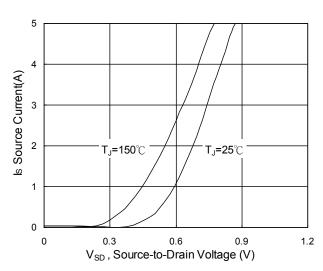


Fig.3 Forward Characteristics of Reverse

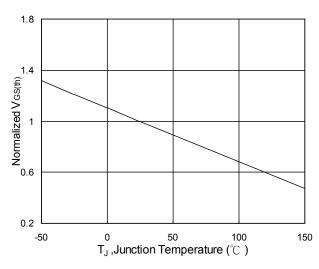


Fig.5 Normalized V_{GS(th)} vs. T_J

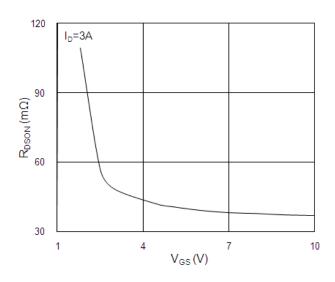


Fig.2 On-Resistance vs. Gate-Source Voltage

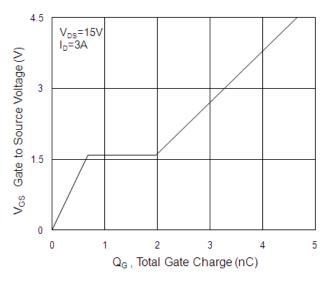


Fig.4 Gate-Charge Characteristics

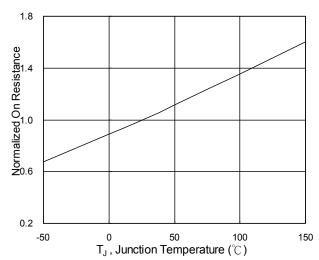
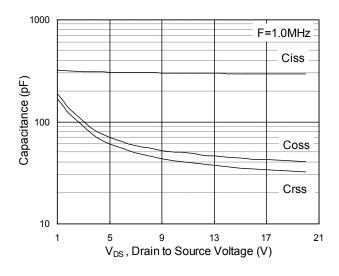


Fig.6 Normalized R_{DSON} vs. T_J





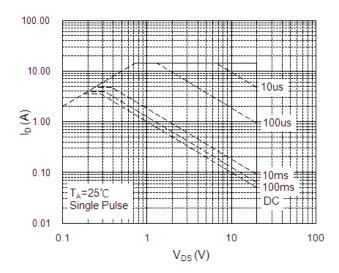


Fig.7 Capacitance

Fig.8 Safe Operating Area

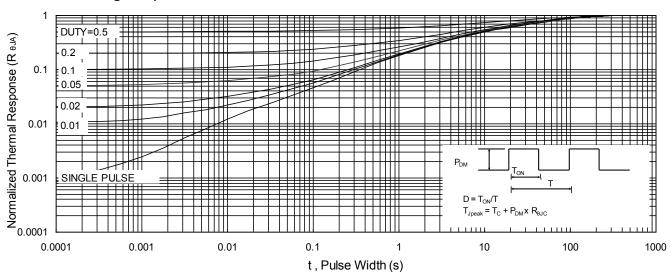
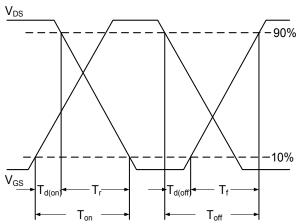


Fig.9 Normalized Maximum Transient Thermal Impedance





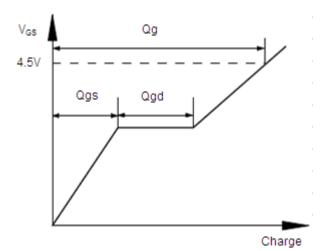
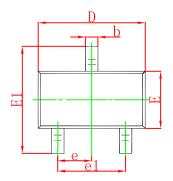
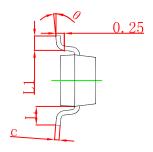


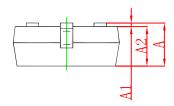
Fig.11 Gate Charge Waveform



SOT-23 Package Outline Dimensions

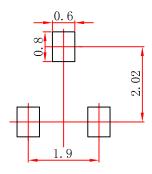






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.

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